Storage Temperature	T_{STG}	-55 to 150	℃
Single Pulse Avalanche Energy	E_{AS}	110	mJ
Diode continuous forward current	I_S@T_C=25℃	55	A

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}				

Gate - Source charge	Q_{gs}	I_D = 5A	-	4	-	
Gate - Drain charge	Q_{gd}	V_{GS} = 10V	-	6	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V, V_{DS}=15V R_G =3.				

Fig.5 On-Resistance VS Gate Source Voltage

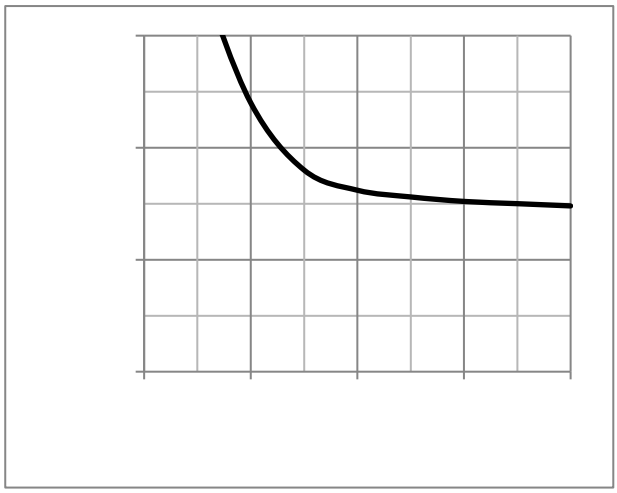


Fig.6 On-Resistance V.S Junction Temperature

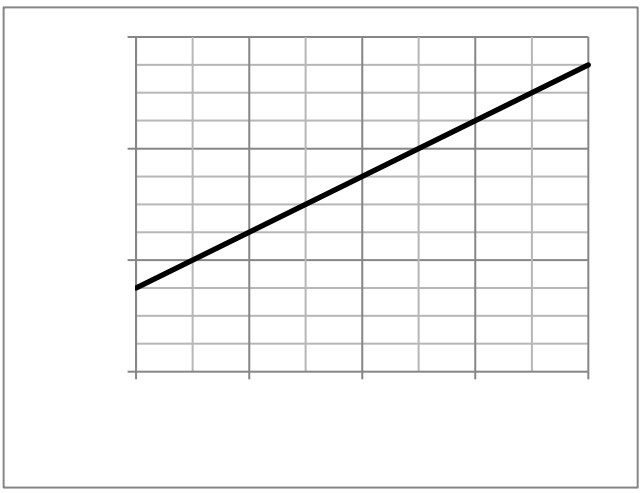


Fig.7 SOA Maximum Safe Operating Area

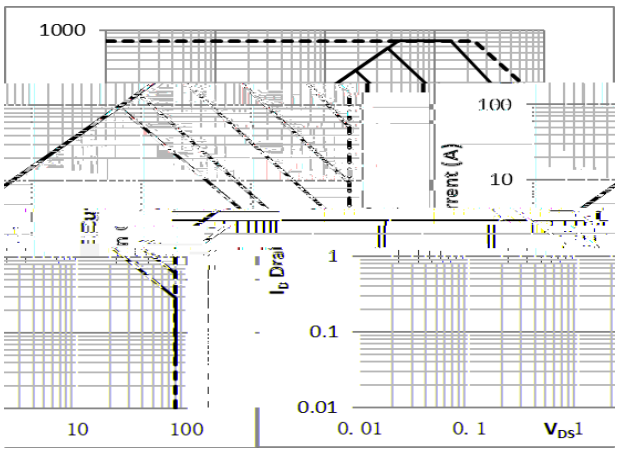


Figure 8. Diode Forward Voltage vs. Current

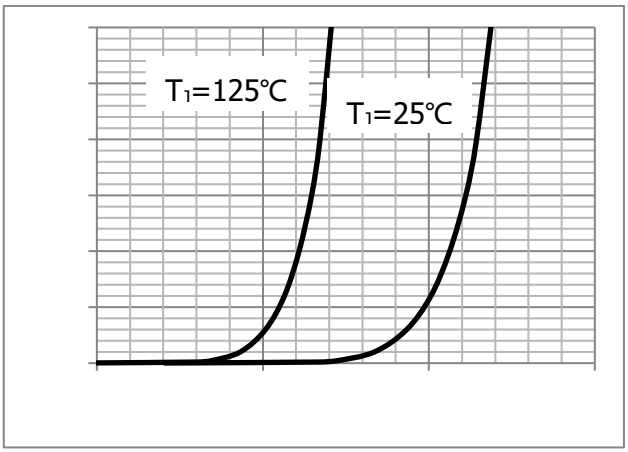


Figure 9. Transfer Characteristics

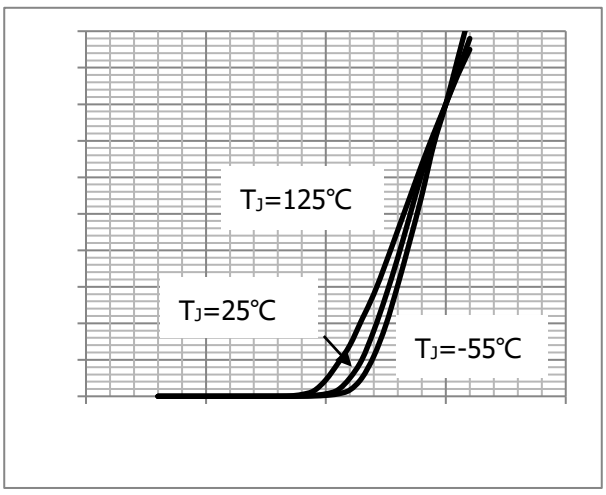


Fig.10 Typical output Characteristics

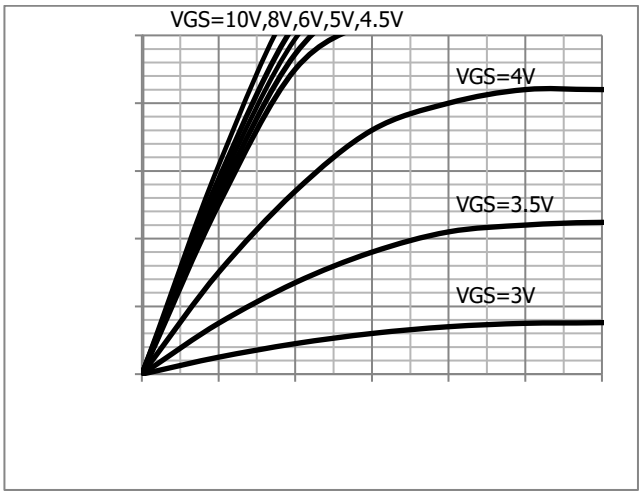
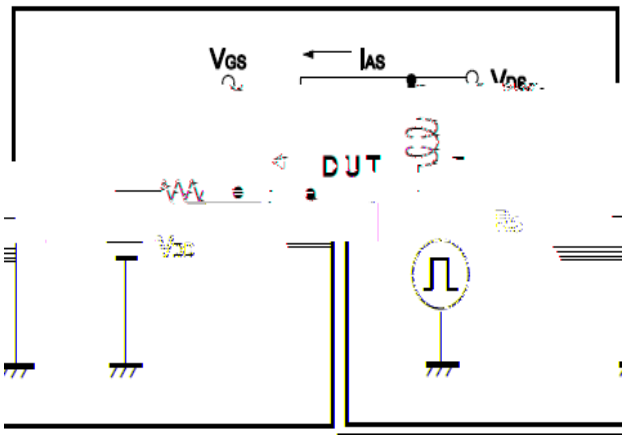
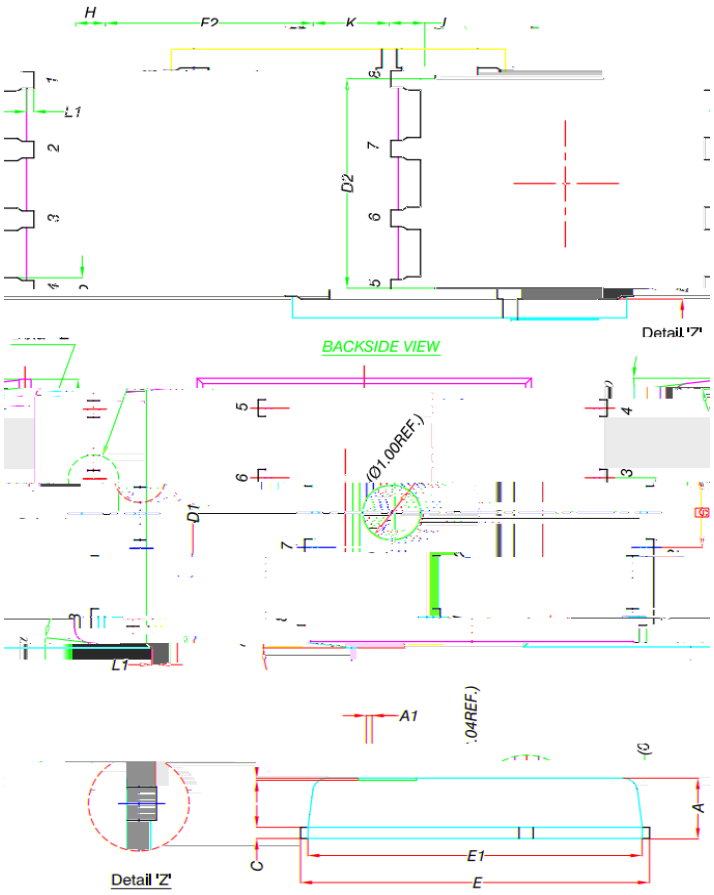


Fig.17 Avalanche Measurement Circuit



sions DFN5×6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.70	5.75	5.80
E2	3.38	3.58	3.78
e		1.27 BSC	
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°	-	12°